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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



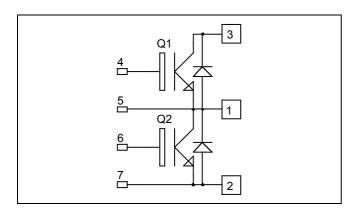






Phase leg Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 600V$$
  
 $I_{C} = 300A$  @  $T_{C} = 80^{\circ}C$ 



#### **Application**

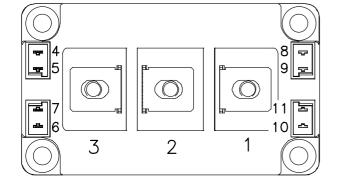
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
$I_{\mathrm{C}}$	Continuous Collector Current	$T_C = 25^{\circ}C$	400	
	Continuous Conector Current	$T_C = 80$ °C	300	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	940	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	600A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				500	μA
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
		$I_C = 300A$ $T_j = 150^{\circ}C$		1.7		v	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4.8 \text{ mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

·	Characteristic Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		18.5		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		1.2		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		0.5		
$Q_{G}$	Gate charge	V <sub>GE</sub> =±15V, I <sub>C</sub> =300A V <sub>CE</sub> =300V		3.2		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		110		ns
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 300A$		490		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$		50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)	)	130		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		60		ns
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 300 \text{A}$		530		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$		70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		3.1		
Lon	Turn on Energy	$V_{\text{Bus}} = 300 \text{V}$ $T_{\text{j}} = 150^{\circ} \text{C}$	2	3.3		mJ
$E_{\text{off}}$	Turn off Energy	$I_C = 300A$ $T_j = 25^{\circ}C$ $R_G = 2.2\Omega$ $T_i = 150^{\circ}C$	1	12 5		1110
			,	12.5		
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 360V$ $t_p \le 6\mu s ; T_j = 150^{\circ}C$		1500		A

Reverse diode ratings and characteristics

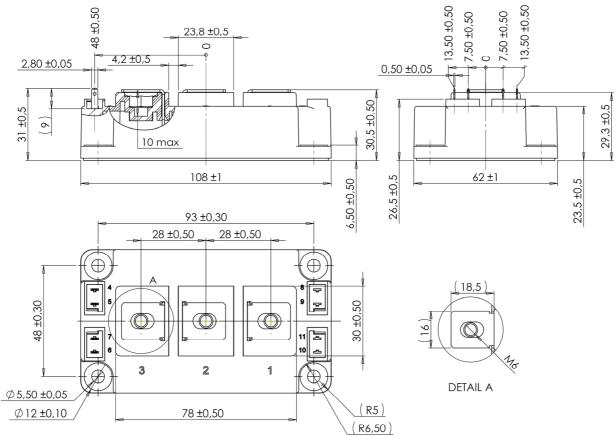
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R=600V$	$T_i = 25$ °C $T_i = 150$ °C			500 750	μΑ
$I_{F}$	DC Forward Current		$Tc = 80^{\circ}C$		300		A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
v <sub>F</sub>			$T_{i} = 150^{\circ}C$		1.5		V
4	Davanga Dagayany Tima		$T_j = 25^{\circ}C$		100		
$t_{rr}$	Reverse Recovery Time		$T_{i} = 150^{\circ}C$		150		ns
0	$I_F = 300A$		$T_j = 25^{\circ}C$		14.4		C
$Q_{rr}$	Reverse Recovery Charge	$V_R = 300V$ di/dt = 4800A/µs	$T_i = 150^{\circ}C$		30.4		μC
Г	D D	αι/αι 1000/1/μ3	$T_j = 25^{\circ}C$		3.4		T
$\mathbf{E}_{\mathrm{rr}}$	E <sub>rr</sub> Reverse Recovery Energy	$T_{\rm j} = 150^{\circ}{\rm C}$		7.2		mJ	



## Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.16	°C/W
1\(\text{thJC}\)			Diode			0.25	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		175		
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight					350	g

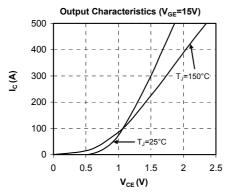
## D3 Package outline (dimensions in mm)

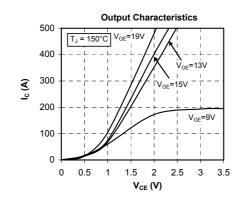


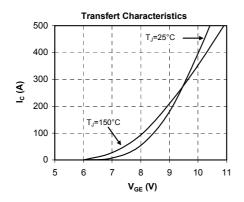
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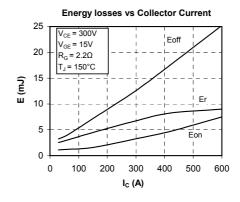


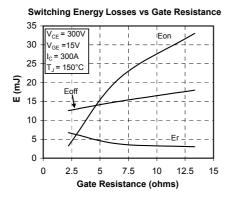
### **Typical Performance Curve**

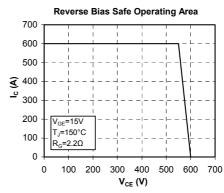


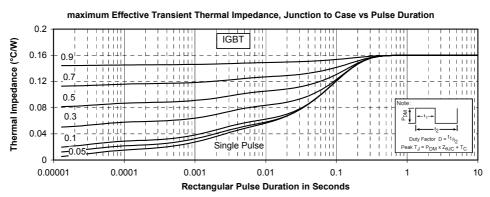






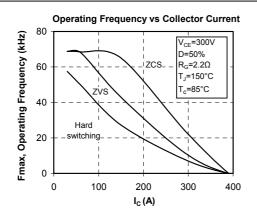


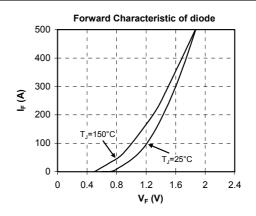


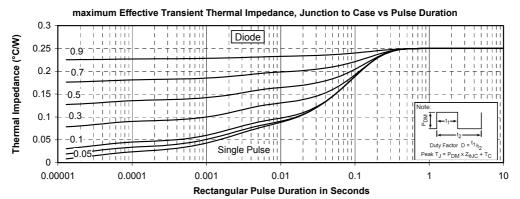


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